

Complementary Darlington Power Transistors

DPAK For Surface Mount Applications

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, convertors, and power amplifiers.

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Available on 16 mm Tape and Reel for Automatic Handling ("T4" Suffix)
- Surface Mount Replacements for 2N6034-2N6039 Series
- Monolithic Construction With Built-in Base-Emitter Shunt Resistors
- High DC Current Gain —
 $h_{FE} = 2500$ (Typ) @ $I_C = 4.0$ Adc
- Complementary Pairs Simplifies Designs

MAXIMUM RATINGS

Rating	Symbol	MJD6036 MJD6039	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CB}	80	Vdc
Emitter-Base Voltage	V_{EB}	5	Vdc
Collector Current — Continuous Peak	I_C	4 8	Adc
Base Current	I_B	100	mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	20 0.16	Watts W/ $^\circ\text{C}$
Total Power Dissipation (1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.75 0.014	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

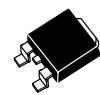
(1) These ratings are applicable when surface mounted on the minimum pad sizes recommended.

THERMAL CHARACTERISTICS

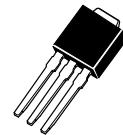
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	6.25	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient (1)	$R_{\theta JA}$	71.4	$^\circ\text{C/W}$

NPN
MJD6036
PNP
MJD6039

SILICON
POWER TRANSISTORS
4 AMPERES
80 VOLTS
20 WATTS

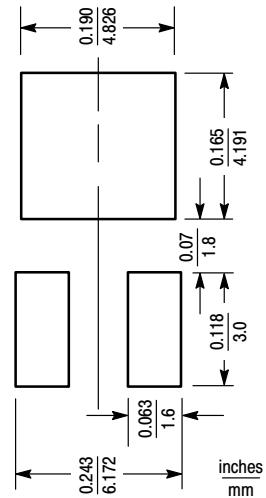


CASE 369A-13



CASE 369-07

MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS



MJD6036 MJD6039

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

*ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage ($I_C = 30 \text{ mA}_\text{dc}$, $I_B = 0$)	$V_{CEO(\text{sus})}$	80	—	Vdc
Collector-Cutoff Current ($V_{CE} = 40 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	—	10	μA_dc
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 1 \text{ Adc}$, $V_{CE} = 4 \text{ Vdc}$) ($I_C = 2 \text{ Adc}$, $V_{CE} = 4 \text{ Vdc}$)	h_{FE}	1000 500	— —	—
Collector-Emitter Saturation Voltage ($I_C = 2 \text{ Adc}$, $I_B = 8 \text{ mA}_\text{dc}$)	$V_{CE(\text{sat})}$	—	2.5	Vdc
Base-Emitter On Voltage ($I_C = 2 \text{ Adc}$, $V_{CE} = 4 \text{ Vdc}$)	$V_{BE(\text{on})}$	—	2.8	Vdc
DYNAMIC CHARACTERISTICS				
Small-Signal Current Gain ($I_C = 0.75 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1 \text{ kHz}$)	h_{fe}	25	—	—
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 0.1 \text{ MHz}$)	C_{ob}	— —	200 100	pF

(1) Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

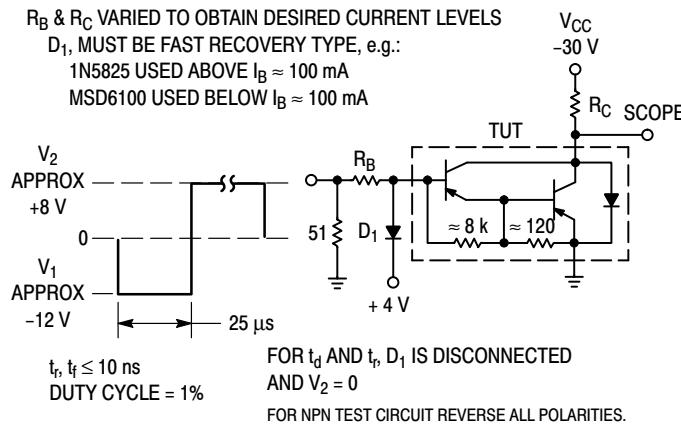


Figure 1. Switching Times Test Circuit

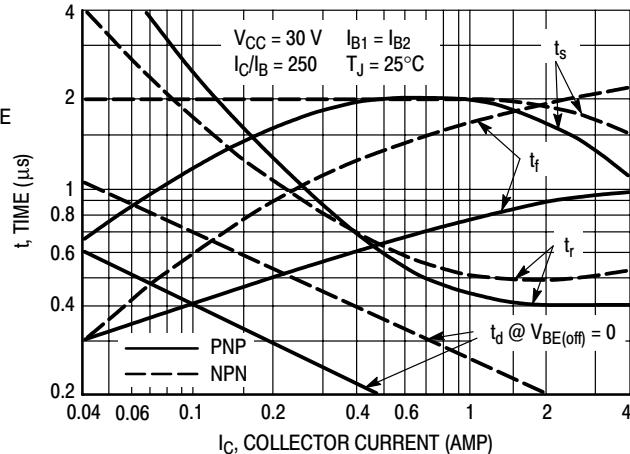


Figure 2. Switching Times

TYPICAL ELECTRICAL CHARACTERISTICS

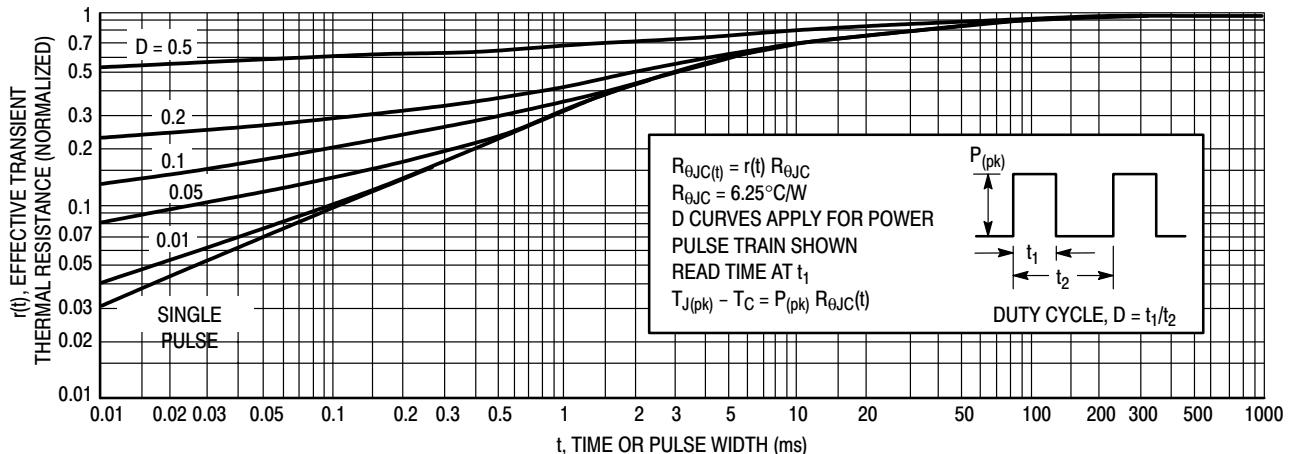


Figure 3. Thermal Response

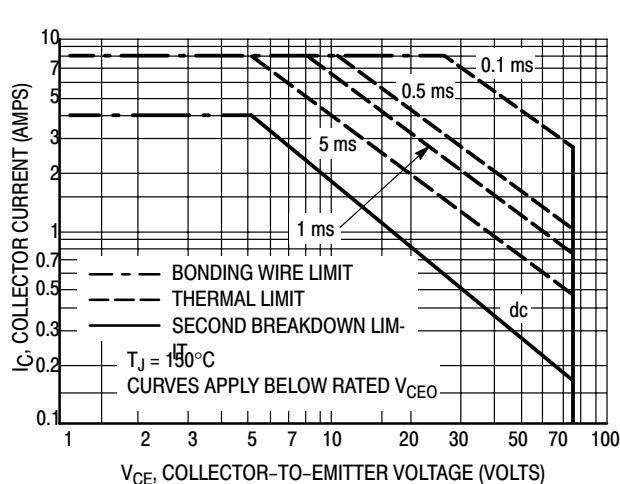


Figure 4. Maximum Rated Forward Biased Safe Operating Area

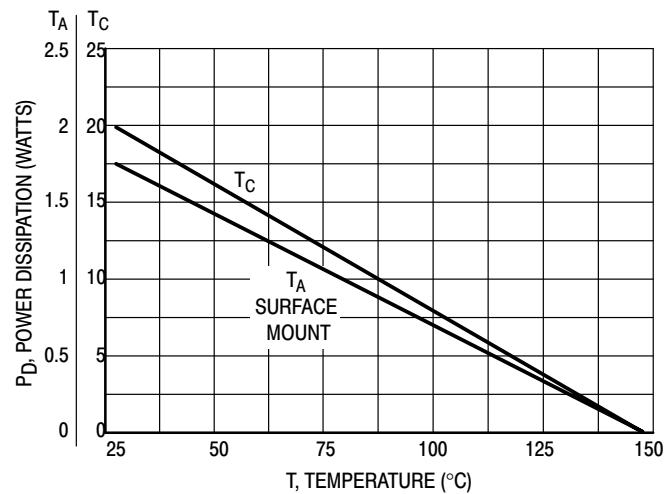


Figure 5. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 6 and 7 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

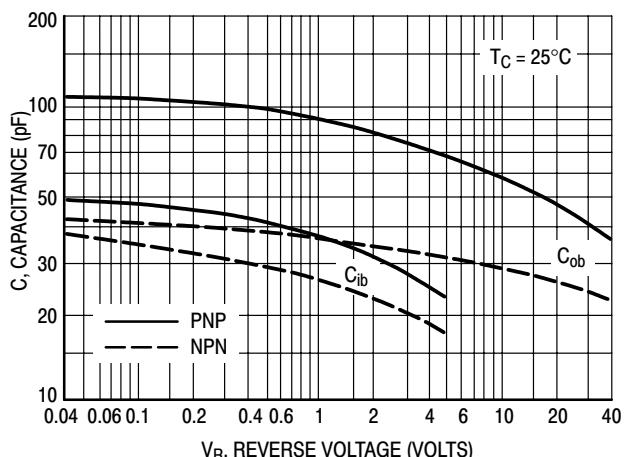
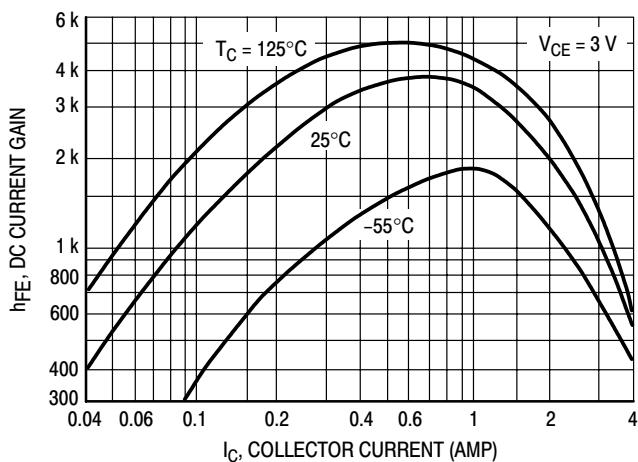


Figure 6. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

PNP MJD6036



NPN MJD6039

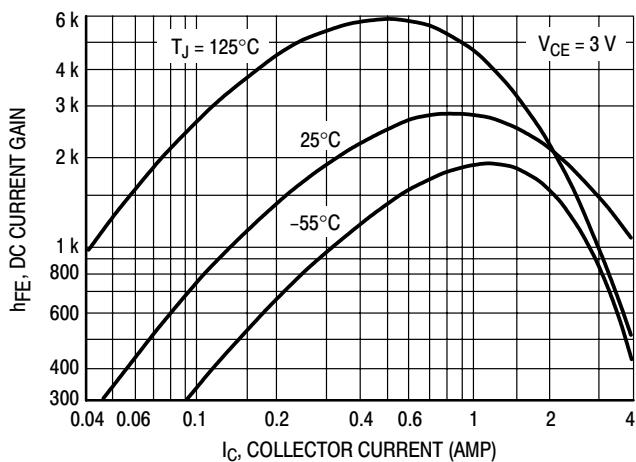


Figure 7. DC Current Gain

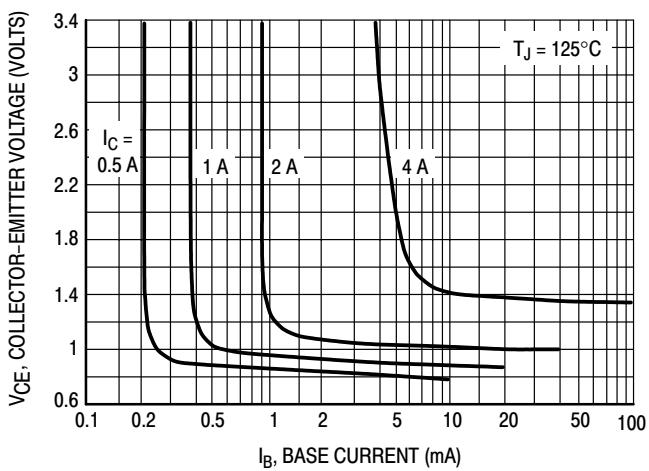
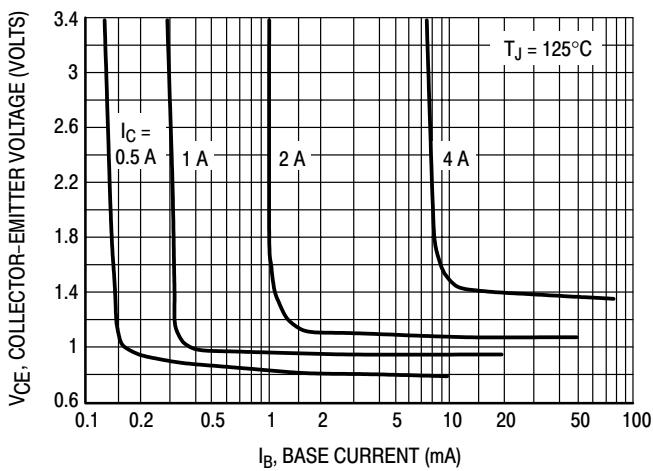


Figure 8. Collector Saturation Region

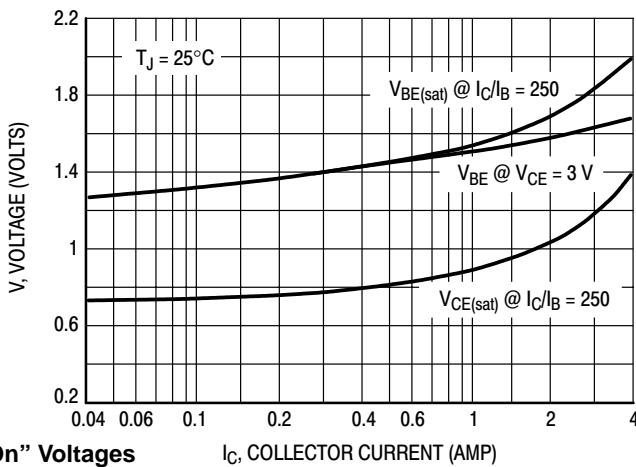
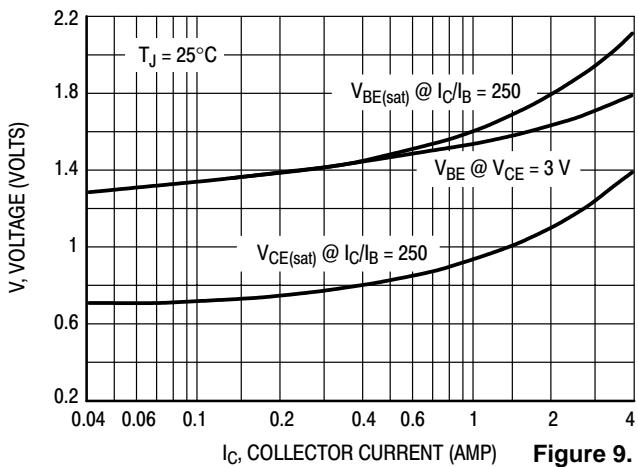
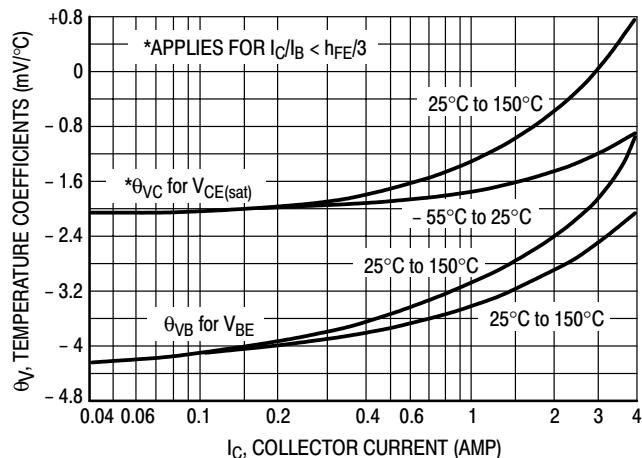


Figure 9. "On" Voltages

MJD6036 MJD6039

PNP MJD6036



NPN MJD6039

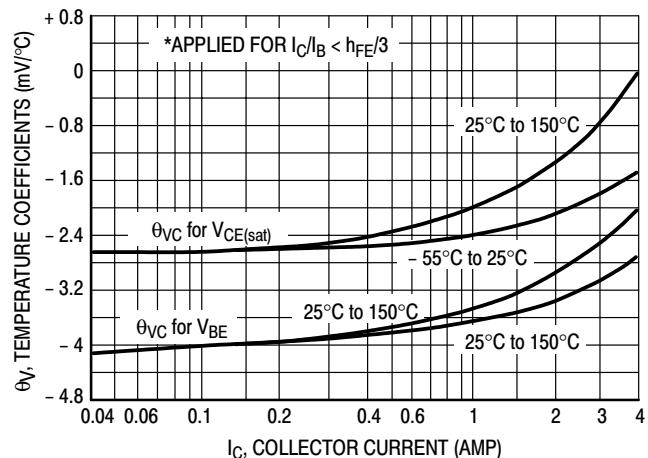


Figure 10. Temperature Coefficients

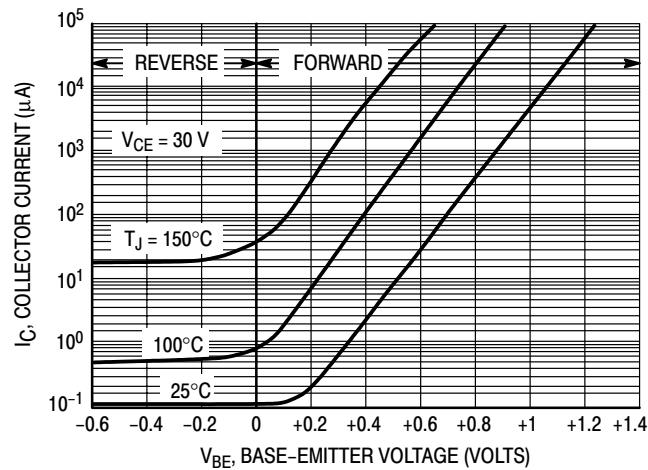
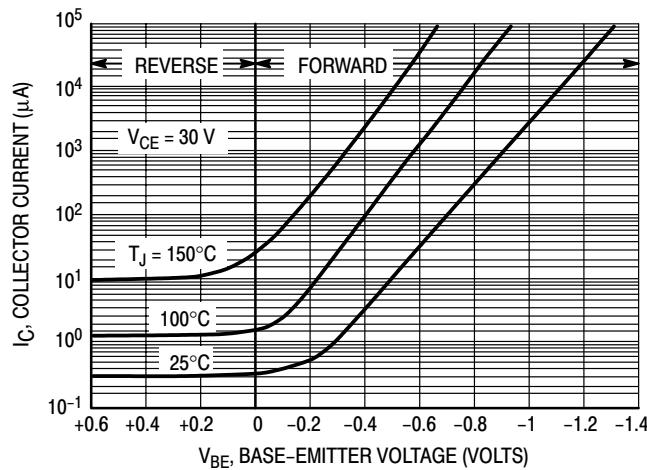


Figure 11. Collector Cut-Off Region

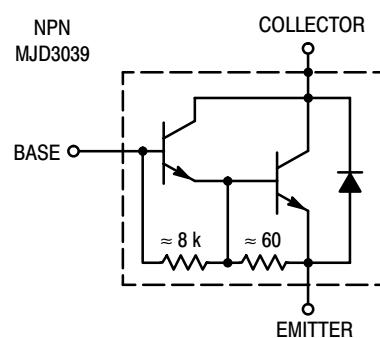
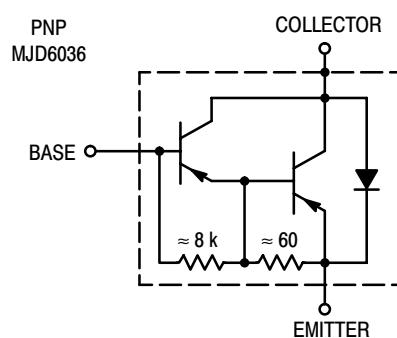
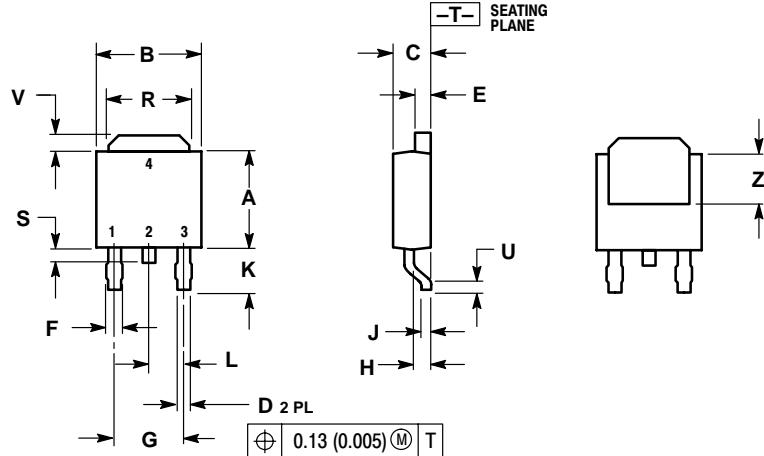


Figure 12. Darlington Schematic

PACKAGE DIMENSIONS

DPAK
CASE 369A-13
ISSUE AA



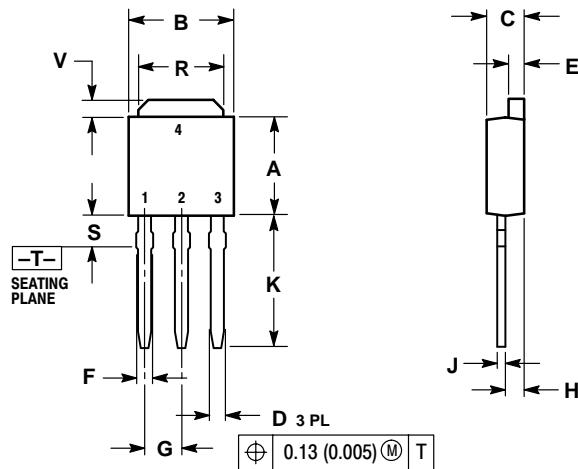
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020	---	0.51	---
V	0.030	0.050	0.77	1.27
Z	0.138	---	3.51	---

PACKAGE DIMENSIONS

DPAK
CASE 369-07
ISSUE M



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com
Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support
German Phone: (+1) 303-308-7140 (Mon–Fri 2:30pm to 7:00pm CET)
Email: ONlit-german@hibbertco.com
French Phone: (+1) 303-308-7141 (Mon–Fri 2:00pm to 7:00pm CET)
Email: ONlit-french@hibbertco.com
English Phone: (+1) 303-308-7142 (Mon–Fri 12:00pm to 5:00pm GMT)
Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781
*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon–Fri 8:00am to 5:00pm MST)
Email: ONlit-spanish@hibbertco.com
Toll-Free from Mexico: Dial 01-800-288-2872 for Access –
then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support
Phone: 1-303-675-2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local
Sales Representative.